

Sandrine Juillaguet

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

125
papers

997
citations

17
h-index

25
g-index

128
ext. papers

1,048
ext. citations

1.5
avg, IF

3.41
L-index

#	Paper	IF	Citations
125	Electrical transport properties of highly doped N-type GaN materials. <i>Semiconductor Science and Technology</i> , 2022 , 37, 055012	1.8	0
124	p-type conductivity in GaN:Zn monocrystals grown by ammonothermal method. <i>Journal of Applied Physics</i> , 2021 , 129, 135702	2.5	1
123	High temperature electrical transport properties of MBE-grown Mg-doped GaN and AlGaN materials. <i>Journal of Applied Physics</i> , 2020 , 128, 085703	2.5	2
122	Electrical transport properties of p-type 4H-SiC. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017 , 214, 1600679	1.6	17
121	High Temperature Annealing of MBE-grown Mg-doped GaN. <i>Journal of Physics: Conference Series</i> , 2017 , 864, 012018	0.3	2
120	Influence of Growth Temperature on Site Competition Effects during Chemical Vapor Deposition of 4H-SiC Layers. <i>Materials Science Forum</i> , 2017 , 897, 79-82	0.4	
119	Optical investigations and strain effect in AlGaIn/GaN epitaxial layers. <i>Journal of Physics: Conference Series</i> , 2017 , 864, 012021	0.3	
118	Comparative Study of p-Type 4H-SiC Grown on n-Type and Semi Insulating 4H-SiC Substrates. <i>Materials Science Forum</i> , 2017 , 897, 275-278	0.4	1
117	Effect of germanium doping on electrical properties of n-type 4H-SiC homoepitaxial layers grown by chemical vapor deposition. <i>Journal of Applied Physics</i> , 2016 , 120, 205701	2.5	5
116	Influence of AlN thickness on AlGaIn epilayer grown by MOCVD. <i>Superlattices and Microstructures</i> , 2016 , 98, 515-521	2.8	4
115	p-Type Doping of 4H- and 3C-SiC Epitaxial Layers with Aluminum. <i>Materials Science Forum</i> , 2016 , 858, 137-142	0.4	13
114	Electrical Transport Properties of Highly Aluminum Doped p-Type 4H-SiC. <i>Materials Science Forum</i> , 2016 , 858, 249-252	0.4	3
113	Study of Geometrical Effects in Charge Pumping Current for Lateral SiC nMOSFETs Electrical Characterization. <i>Materials Science Forum</i> , 2015 , 821-823, 717-720	0.4	
112	Optical Characterization of p-Type 4H-SiC Epilayers. <i>Materials Science Forum</i> , 2015 , 821-823, 249-252	0.4	1
111	Structural properties and dielectric function of graphene grown by high-temperature sublimation on 4H-SiC(000-1). <i>Journal of Applied Physics</i> , 2015 , 117, 085701	2.5	12
110	Influence of Site Competition Effects on Dopant Incorporation during Chemical Vapor Deposition of 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2015 , 821-823, 149-152	0.4	1
109	Nitrogen Incorporation during Seeded Sublimation Growth of 4H-SiC and 6H-SiC. <i>Materials Science Forum</i> , 2015 , 821-823, 60-63	0.4	2

108	Comparative Study of n-Type 4H-SiC: Raman vs Photoluminescence Spectroscopy. <i>Materials Science Forum</i> , 2015 , 821-823, 237-240	0.4	
107	Raman Investigation of Heavily Al Doped 4H-SiC Layers Grown by CVD. <i>Materials Science Forum</i> , 2014 , 806, 51-55	0.4	3
106	Ge incorporation inside 4H-SiC during homoepitaxial growth by chemical vapor deposition. <i>Acta Materialia</i> , 2014 , 75, 219-226	8.4	11
105	Investigation of Aluminum Incorporation in 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2014 , 806, 45-50	0.4	2
104	Characterization of Ge-Doped Homoepitaxial Layers Grown by Chemical Vapor Deposition. <i>Materials Science Forum</i> , 2014 , 778-780, 261-264	0.4	7
103	Optical Investigation of 3C-SiC Hetero-Epitaxial Layers Grown by Sublimation Epitaxy under Gas Atmosphere. <i>Materials Science Forum</i> , 2014 , 778-780, 243-246	0.4	
102	Raman Investigation of Aluminum-Doped 4H-SiC. <i>Materials Science Forum</i> , 2013 , 740-742, 357-360	0.4	4
101	Stacking faults in intrinsic and N-doped 4H-SiC: true influence of the N-doping on their multiplicity. <i>Philosophical Magazine</i> , 2013 , 93, 1317-1325	1.6	6
100	Comparative micro-photoluminescence investigation of ZnO hexagonal nanopillars and the seeding layer grown on 4H-SiC. <i>Journal of Luminescence</i> , 2012 , 132, 122-127	3.8	1
99	Room temperature luminescence properties of fluorescent SiC as white light emitting diode medium. <i>Thin Solid Films</i> , 2012 , 522, 33-35	2.2	9
98	Low Temperature Photoluminescence Signature of Stacking Faults in 6H-SiC Epilayers Grown on Low Angle Off-Axis Substrates. <i>Materials Science Forum</i> , 2012 , 717-720, 407-410	0.4	
97	Cubic SiC formation on the C-face of 6H-SiC (0001) substrates. <i>Journal of Crystal Growth</i> , 2012 , 348, 91-96	1.6	16
96	Impact of extended defects on Hall and magnetoresistivity effects in cubic silicon carbide. <i>Journal Physics D: Applied Physics</i> , 2012 , 45, 225102	3	5
95	Fluorescent silicon carbide as an ultraviolet-to-visible light converter by control of donor to acceptor recombinations. <i>Journal Physics D: Applied Physics</i> , 2012 , 45, 235107	3	8
94	Shockley-Frank stacking faults in 6H-SiC. <i>Journal of Applied Physics</i> , 2012 , 111, 113527	2.5	5
93	Low Temperature Photoluminescence Investigation of 3-Inch SiC Wafers for Power Device Applications. <i>Materials Science Forum</i> , 2012 , 711, 164-168	0.4	1
92	Seeding Layer Influence on the Low Temperature Photoluminescence Intensity of 3C-SiC Grown on 6H-SiC by Sublimation Epitaxy. <i>Materials Science Forum</i> , 2012 , 711, 149-153	0.4	2
91	Optical Properties of As-Grown and Process-Induced Stacking Faults in 4H-SiC 2011 , 205-242		

90	Optical Investigation of Defect Filtering Effects in Bulk 3C-SiC Crystals Grown by the CF-PVT Method Using a Necking Technique. <i>Materials Science Forum</i> , 2011 , 679-680, 169-172	0.4	
89	Splitting of type-I (N-B, P-Al) and type-II (N-Al, N-Ga) donor-acceptor pair spectra in 3C-SiC. <i>Physical Review B</i> , 2011 , 83,	3.3	3
88	Effect of initial substrate conditions on growth of cubic silicon carbide. <i>Journal of Crystal Growth</i> , 2011 , 324, 7-14	1.6	29
87	Effect of Inter-Well Coupling between 3C and 6H in-Grown Stacking Faults in 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2011 , 679-680, 314-317	0.4	1
86	Structural and Optical Investigation of VLS Grown (111) 3C-SiC Layers on 6H-SiC Substrates in Sn-Based Melts. <i>Materials Science Forum</i> , 2011 , 679-680, 165-168	0.4	
85	Influence of Post-Growth Annealing on the Defects Nature and Distribution in VLS Grown (111) 3C-SiC Layers. <i>Materials Science Forum</i> , 2011 , 679-680, 241-244	0.4	2
84	Optical Characterization of VLS+CVD Grown 3C-SiC Films by Non-Linear and Photoluminescence Techniques. <i>Materials Science Forum</i> , 2010 , 645-648, 443-446	0.4	6
83	Investigation of Low Doped n-Type and p-Type 3C-SiC Layers Grown on 6H-SiC Substrates by Sublimation Epitaxy. <i>Materials Science Forum</i> , 2010 , 645-648, 179-182	0.4	1
82	6H-Type Zigzag Faults in Low-Doped 4H-SiC Epitaxial Layers. <i>Materials Science Forum</i> , 2010 , 645-648, 347-350	0.4	5
81	TEM and LTPL Investigations of 3C-SiC Layers Grown by LPE on (100) and (111) 3C-SiC Seeds. <i>Materials Science Forum</i> , 2010 , 645-648, 383-386	0.4	1
80	Low Doped 3C-SiC Layers Deposited by the Vapour-Liquid-Solid Mechanism on 6H-SiC Substrates. <i>Materials Science Forum</i> , 2010 , 645-648, 171-174	0.4	6
79	LTPL Investigation of N-Ga and N-Al Donor-Acceptor Pair Spectra in 3C-SiC Layers Grown by VLS on 6H-SiC Substrates. <i>Materials Science Forum</i> , 2010 , 645-648, 415-418	0.4	2
78	Influence of the C/Si Ratio on the Dopant Concentration and Defects in CVD Grown 3C-SiC Homoepitaxial Layers 2010 ,		3
77	Combined effects of Ga, N, and Al codoping in solution grown 3C-SiC. <i>Journal of Applied Physics</i> , 2010 , 108, 013503	2.5	10
76	8H Stacking Faults in a 4H-SiC Matrix: Simple Unit Cell or Double 3C Quantum Well?. <i>Materials Science Forum</i> , 2009 , 615-617, 339-342	0.4	2
75	Photoluminescence-Topography of the p-Type Doped SiC Wafers for Determination of Doping Inhomogeneity. <i>Materials Science Forum</i> , 2009 , 615-617, 259-262	0.4	0
74	Nitrogen Doping of 3C-SiC Single Crystals Grown by CF-PVT. <i>Materials Science Forum</i> , 2009 , 615-617, 45-48	0.4	1
73	Advances in Liquid Phase Conversion of (100) and (111) Oriented Si Wafers into Self-Standing 3C-SiC. <i>Materials Science Forum</i> , 2009 , 615-617, 49-52	0.4	1

72	Optical investigation of stacking faults in 4H-SiC epitaxial layers: Comparison of 3C and 8H polytypes. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2009 , 165, 5-8	3.1	4
71	Combined structural and optical studies of stacking faults in 4H-SiC layers grown by chemical vapour deposition. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2009 , 206, 1924-1930	1.6	7
70	Defect-induced polytype transformations in LPE grown SiC epilayers on (1 1 1) 3C-SiC seeds grown by VLS on 6H-SiC. <i>Physica B: Condensed Matter</i> , 2009 , 404, 4727-4730	2.8	1
69	Quantum confinement effect of ZnO nanocrystallites embedded in In ₂ O ₃ films. <i>Journal of Applied Physics</i> , 2008 , 104, 084906	2.5	2
68	Optical properties of as-grown and process-induced stacking faults in 4H-SiC. <i>Physica Status Solidi (B): Basic Research</i> , 2008 , 245, 1337-1355	1.3	14
67	Prospects for 3C-SiC bulk crystal growth. <i>Journal of Crystal Growth</i> , 2008 , 310, 976-981	1.6	35
66	Nitrogen doping of 3C-SiC thin films grown by CVD in a resistively heated horizontal hot-wall reactor. <i>Journal of Crystal Growth</i> , 2008 , 310, 3174-3182	1.6	37
65	Photoluminescence, cathodo-luminescence and micro-Raman spectroscopy of as-grown stacking faults in 4H-SiC. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 1513-1516		
64	Doping effect on the optical properties of ZnO nanostructures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 1432-1437		5
63	Strain and wafer curvature of 3C-SiC films on silicon: influence of the growth conditions. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 981-986	1.6	51
62	Cathodoluminescence investigation of stacking faults extension in 4H-SiC. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2007 , 204, 2222-2228	1.6	5
61	Optical investigation methods for SiC device development: application to stacking faults diagnostic in active epitaxial layers. <i>Journal Physics D: Applied Physics</i> , 2007 , 40, 6264-6277	3	20
60	Nonlinear dependence of the magnetophotoluminescence energies of asymmetric GaAs _{0.67} Al _{0.33} As quantum wells on an external magnetic field. <i>Physical Review B</i> , 2007 , 75,	3.3	6
59	Screening the built-in electric field in 4H silicon carbide stacking faults. <i>Applied Physics Letters</i> , 2007 , 90, 111902	3.4	8
58	Electric-Field Screening Effects in the Micro-Photoluminescence Spectra of As-Grown Stacking Faults in 4H-SiC. <i>Materials Science Forum</i> , 2007 , 556-557, 351-354	0.4	
57	Growth and Characterization of ¹³ C Enriched 4H-SiC for Fundamental Materials Studies. <i>Materials Science Forum</i> , 2007 , 556-557, 13-16	0.4	4
56	Application of LTPL Investigation Methods to CVD-Grown SiC. <i>Chemical Vapor Deposition</i> , 2006 , 12, 549-556		38
55	Results of SIMS, LTPL and Temperature-Dependent Hall Effect Measurements Performed on Al-Doped SiC Substrates Grown by the M-PVT Method. <i>Materials Science Forum</i> , 2006 , 527-529, 633-636	0.4	6

54	Characterization of Bulk 3C-SiC Single Crystals Grown on 4H-SiC by the CF-PVT Method. <i>Materials Science Forum</i> , 2006 , 527-529, 99-102	0.4	12
53	Single-Domain 3C-SiC Epitaxially Grown on 6H-SiC by the VLS Mechanism. <i>Materials Science Forum</i> , 2006 , 527-529, 287-290	0.4	6
52	Characterization of a 3C-SiC Single Domain Grown on 6H-SiC(0001) by a Vapor-Liquid-Solid Mechanism. <i>Crystal Growth and Design</i> , 2006 , 6, 2598-2602	3.5	27
51	Specific Aspects of Type II Heteropolytype Stacking Faults in SiC. <i>Materials Science Forum</i> , 2005 , 483-485, 335-340	0.4	16
50	Fabrication and characterization of high quality undoped and Ga ₂ O ₃ -doped ZnO thin films by reactive electron beam co-evaporation technique. <i>Journal of Crystal Growth</i> , 2005 , 275, 512-520	1.6	53
49	Optical properties of Ga ₂ O ₃ doped ZnO nanoribbons. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 1314-1318		16
48	Control of 3C-SiC/Si wafer bending by the checker-board carbonization method. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 524-530	1.6	17
47	Control of epitaxial layers grown on 4H-SiC: from 3C microcrystalline inclusions to type II quantum well structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 593-597	1.6	3
46	Technical aspects of $11\bar{2}0$ 4H-SiC MOSFET processing. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2005 , 202, 680-685	1.6	1
45	Intensity Ratio of the Doublet Signature of Excitons Bound to 3C-SiC Stacking Faults in a 4H-SiC Matrix. <i>Materials Science Forum</i> , 2005 , 483-485, 331-334	0.4	9
44	Excitation Power Dependence of Al-Related Features in the LTPL Spectra of 4H-SiC. <i>Materials Science Forum</i> , 2005 , 483-485, 449-452	0.4	2
43	Comparative Evaluation of Free-Standing 3C-SiC Crystals. <i>Materials Science Forum</i> , 2005 , 483-485, 229-232	0.4	5
42	Evaluation of p-Type Doping for (1,1,-2,0) Epitaxial Layers Grown on a-Cut (1,1,-2,0) 4H-SiC Substrates. <i>Materials Science Forum</i> , 2005 , 483-485, 117-120	0.4	1
41	Dilute Aluminium Concentration in 4H-SiC: from SIMS to LTPL Measurements. <i>Materials Science Forum</i> , 2004 , 457-460, 775-778	0.4	14
40	Characterization of Thick 2-Inch 4H-SiC Layers Grown by the Continuous Feed-Physical Vapor Transport Method. <i>Materials Science Forum</i> , 2004 , 457-460, 91-94	0.4	6
39	Investigation of Epitaxial Layers Grown on a-Cut 4H-SiC Substrates. <i>Materials Science Forum</i> , 2004 , 457-460, 237-240	0.4	5
38	Comparative Studies of 4H-SiC Layers Grown with Either Silane or HexamethylDisilane / Propane Precursor Systems. <i>Materials Science Forum</i> , 2004 , 457-460, 217-220	0.4	9
37	Optical Investigation of Stacking Faults and Micro-Crystalline Inclusions In-Low-Doped 4H-SiC Layers. <i>Materials Science Forum</i> , 2004 , 457-460, 577-580	0.4	9

36	Investigation of 2 Inch SiC Layers Grown in a Resistively-Heated LP-CVD Reactor with Horizontal "Hot-Walls". <i>Materials Science Forum</i> , 2004 , 457-460, 273-276	0.4	29
35	Effect of SiN treatment on GaN epilayer quality. <i>Physica Status Solidi A</i> , 2004 , 201, 502-508		26
34	Optical properties of GaN grown on porous silicon substrate. <i>Physica Status Solidi A</i> , 2004 , 201, 582-587		12
33	Nontrivial carrier recombination dynamics and optical properties of over-excited GaN/AlN quantum dots. <i>Physica Status Solidi (B): Basic Research</i> , 2004 , 241, 2779-2782	1.3	1
32	Influence of silane flow on MOVPE grown GaN on sapphire substrate by an in situ SiN treatment. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004 , 110, 251-255	3.1	28
31	Hexamethyldisilane/propane versus silane/propane precursors: application to the growth of high-quality 3C-SiC on Si. <i>Semiconductor Science and Technology</i> , 2003 , 18, 1015-1023	1.8	26
30	Optical properties of GaN/AlN quantum boxes under high photo-excitation. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2003 , 2666-2669		1
29	Growth at High Rates and Characterization of Bulk 3C-SiC Material. <i>Materials Science Forum</i> , 2003 , 433-436, 115-118	0.4	9
28	Discrete states of conduction electrons bound to magnetoacceptors in quantum wells. <i>Physical Review B</i> , 2003 , 68,	3.3	5
27	4H-SiC Material for Hall Effect and High-Temperature Sensors Working in Harsh Environments. <i>Materials Science Forum</i> , 2002 , 389-393, 1435-1438	0.4	5
26	Investigation of porous silicon as a new compliant substrate for 3C-SiC deposition. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 571-575	3.1	12
25	Optical investigation of residual doping species in 6H and 4H-SiC layers grown by chemical vapor deposition. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 253-257	3.1	9
24	Optical assessment of purity improvement effects in bulk 6H and 4H-SiC wafers grown by physical vapor transport. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1999 , 61-62, 258-264	3.1	8
23	Optical Properties of As-Grown, α -Particle Irradiated and N ⁺ -Ion Implanted GaN. <i>Physica Status Solidi (B): Basic Research</i> , 1999 , 216, 619-623	1.3	5
22	Oscillations of 2D electron density in GaAs/Ga _{0.67} Al _{0.33} As heterostructures in the QHE regime. <i>Semiconductor Science and Technology</i> , 1999 , 14, 915-920	1.8	9
21	Experimental Investigation of 4H-SiC Bulk Crystal Growth. <i>Materials Science Forum</i> , 1998 , 264-268, 17-20	0.4	5
20	Raman, Low Temperature Photoluminescence and Transport Investigation of N-Implanted 6H-SiC. <i>Materials Science Forum</i> , 1998 , 264-268, 725-728	0.4	
19	Optical Properties of InGaN/GaN Multiple Quantum Wells. <i>Materials Science Forum</i> , 1998 , 264-268, 1295-1298	0.4	2

18	Time-resolved photoluminescence studies of InGaN/GaN multiple quantum wells. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 1997 , 2, 1		10
17	Photoluminescence investigation of a degenerate two-dimensional electron gas in GaN/AlGaIn heterojunction. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997 , 43, 211-214	3.1	4
16	Phonon strain-shift coefficients of Si _{1-x} Ge _x grown on Ge(001). <i>Physical Review B</i> , 1996 , 53, 6923-6926	3.3	33
15	Strong element dependence of C 1s and Si 2p X-ray photoelectron diffraction profiles for identical C and Si local geometries in β -SiC. <i>Surface Science</i> , 1995 , 339, 363-371	1.8	20
14	Optical tools for intermixing diagnostic: application to InGaAs/InGaAsP microstructures. <i>Applied Surface Science</i> , 1993 , 63, 177-181	6.7	3
13	Interface characterization of strained InGaAs/InP quantum wells after a growth interruption sequence. <i>Applied Surface Science</i> , 1993 , 63, 187-190	6.7	7
12	Growth and characterization of In _{0.53} Ga _{0.47} As/In _x Ga _{1-x} As strained-layer superlattices. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1993 , 21, 244-248	3.1	3
11	Evidence for non-uniform interface thickness in strained InGaAs/InP quantum wells. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1993 , 20, 62-65	3.1	2
10	Non-destructive approaches to interdiffusion phenomena across GaInAs/GaInAsP interfaces: photoluminescence vs. Raman. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1993 , 20, 73-76	3.1	
9	Morphology of InGaAs/InP QWs : from excitonic spectroscopy to HR-TEM analyses. <i>European Physical Journal Special Topics</i> , 1993 , 03, 99-106		2
8	Growth and characterization of In _{0.53} Ga _{0.47} As/In _x Ga _{1-x} As strained-layer superlattices. <i>European Materials Research Society Symposia Proceedings</i> , 1993 , 40, 244-248		
7	Interface characterization of strained InGaAs/InP quantum wells after a growth interruption sequence 1993 , 187-190		
6	Interface properties of strained InGaAs/InP quantum wells grown by LP-MOVPE. <i>Microelectronic Engineering</i> , 1992 , 19, 891-894	2.5	3
5	QUANTITATIVE APPROACH OF NON-STOICHIOMETRIC INTERFACES FOLLOWING A GROWTH INTERRUPTION SEQUENCE: APPLICATION TO LATTICE-MATCHED InGaAs/InP QUANTUM WELLS 1992 , 155-160		2
4	Optical characterization of strained InGaAs/InP quantum well structures 1992 , 161-166		2
3	Optical characterization of strained InGaAs/InP quantum well structures. <i>Microelectronic Engineering</i> , 1991 , 15, 593-596	2.5	4
2	Finite interface effects for thin GaInAs/InP quantum wells grown by LP-MOVPE with a growth interruption sequence. <i>Journal of Crystal Growth</i> , 1991 , 107, 543-548	1.6	38
1	Investigation of residual impurity content in GaAs layers grown by VPE under very low pressure conditions. <i>Journal of Electronic Materials</i> , 1991 , 20, 79-90	1.9	1

